NSN 5962-01-051-2110

Memory Microcircuit - Page 1 of 2

View Online at https://aerobasegroup.com/nsn/5962-01-051-2110

Body Length:

Between 0.745 inches and 0.785 inches

Body Width:

Between 0.240 inches and 0.280 inches

Body Height:

Between 0.120 inches and 0.160 inches

Maximum Power Dissipation Rating:

625.0 milliwatts

Operating Tempurature Range:

+0.0/+75.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Cheyenne missile model 427m

Features Provided:

Hermetically sealed and monolithic and positive outputs and bipolar and 3-state output and w/enable and w/storage and w/buffered output and w/decoded output and w/disable and programmable and programmed

Inclosure Material:

Ceramic and glass

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

10 input

Case Outline Source And Designator:

-0-001-ae joint electron device engineering council

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Time Rating Per Chacteristic:

35.00 nanoseconds propagation delay time, low to high level output and 35.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Prom

Memory Capacity:

Unknown

Test Data Document:

11530-311325 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

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